

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	12	438/118-119	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/06/17 08:12
L2	2270	438/118	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 08:12
L3	736	438/119	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 08:13
L4	1018	257/782	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 08:13
L5	1648	257/783	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 08:13
L6	405	219/635	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 08:14
L7	182	219/603	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 08:14
L8	75	219/616	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 08:14

L9	70	219/651	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 08:14
L10	74	219/673	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 08:14
L11	102	219/677	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 08:14
L12	4927	2 3 4 5 6 7 8 9 10 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 08:14
L13	510	12 and (induct\$3 near3 heat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 08:16
L14	53	13 and (solder eutectic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 08:16
L15	12	13 and ((chip die (semiconductor near1 (component device element package)) dice) with (substrate carrier pcb board))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 08:18
L16	0	("5558795").URPN.	USPAT	OR	ON	2005/06/17 08:33
L17	15	("3706176"   "3781978"   "3783218"   "3872275"   "4069498"   "4079511"   "4154998"   "4224494"   "4251852"   "4380484"   "4552300"   "4740663"   "4757175"   "4814943"   "5182424").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/17 08:33

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	29	(US-6288376-\$ or US-6386422-\$ or US-6686565-\$ or US-5573688-\$ or US-5520320-\$ or US-5193735-\$ or US-5066850-\$ or US-4817851-\$ or US-4750664-\$ or US-4568277-\$ or US-5785233-\$ or US-5440101-\$ or US-5433368-\$ or US-5154338-\$ or US-4938410-\$ or US-6138893-\$ or US-5524810-\$ or US-5345061-\$ or US-5338008-\$ or US-5230460-\$ or US-6135344-\$ or US-4983804-\$ or US-6275750-\$ or US-6423945-\$ or US-5409543-\$ or US-4687895-\$).did. or (US-5492265-\$ or US-6794275-\$ or US-6608291-\$).did.	USPAT	OR	ON	2005/06/17 14:07
L2	8	1 and ceramic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:13
L3	0	"6608291".pn. and ceramic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:29
L4	445	(hot near plate) near3 (ceramic alumina (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:30
L5	3273	(die near1 (attachment attached attach bonded bond bonding)) near3 (method process)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:18
L6	1	4 and 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:18

L7	18904	((die dice chip) near3 (attachment attached attach bonded bond bonding)) near4 (carrier substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:18
L8	3	4 and 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:20
L9	24879	((die dice chip) near3 (attachment attached attach bonded bond bonding soldering soldered)) near4 (carrier board substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:45
L10	4	4 and 9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:22
L11	55388	(induct\$3 near1 heat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:21
L12	19	4 and 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:22
L13	1	4 with (semiconductor chip die) with (bond\$3 attach\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:31
L14	508	(hot near plate) near4 (ceramic alumina (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:30

L15	84	14 with (semiconductor chip die)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:44
L16	54	15 and solder and (substrate carrier board)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:35
L17	30	14 and (heating with (furnace tunnel system))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:36
L18	201	14 and (semiconductor chip die)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:44
L19	157	18 and (attachment attached attach bonded bond bonding soldering soldered)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:45
L20	32	18 and ((attachment attached attach bonded bond bonding soldering soldered) near4 (carrier board substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:46
L21	2	18 and (reflow near3 soldering)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:47
L22	2	14 and (reflow near3 soldering)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:48

L23	7	14 and (heating near zone)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/17 14:48
-----	---	----------------------------	---	----	----	------------------